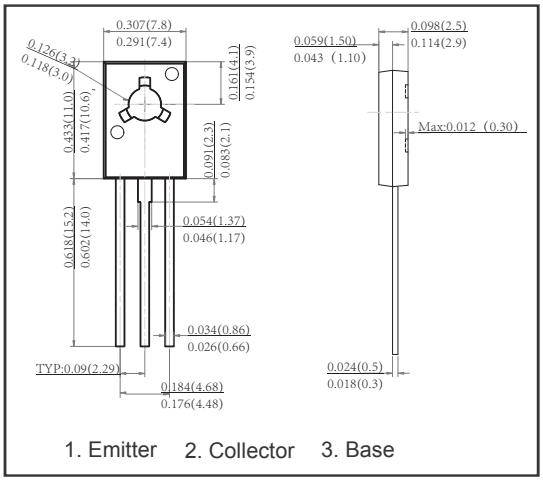
TO-126 Plastic-Encapsulate Transistors

FEATURES

- High Current
- TRANSISTOR (NPN)
- Complement To BD136, BD138 And BD140

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter		Symbol	Value	Unit
Collector-Base Voltage	BD135 BD137	V_{CBO}	45 60	V
Collector-Emitter Voltage	BD135 BD137	V_{CEO}	45 60	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	1.5	A
Collector Power Dissipation		P_C	1.25	W
Thermal Resistance From Junction To Ambient		$R_{\theta JA}$	100	℃/W
Junction Temperature		T_j	150	℃
Storage Temperature		T_{stg}	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	**BD135** **BD137**	$V_{(BR)CBO}$	I_C= 0.1mA,I_E=0	45 60			V
Collector-emitter sustaining voltage	**BD135** **BD137**	$V_{CEO(SUS)}$	I_C=0.03A,I_B=0	45 60			V
Emitter-base breakdown voltage		$V_{(BR)EBO}$	I_E=0.1mA,I_C=0	5			V
Collector cut-off current		I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current		I_{EBO}	V_{EB}=5V,I_C=0			10	μA
DC current gain		$h_{FE(1)}$	V_{CE}=2V, I_C=150mA	40		250	
		$h_{FE(2)}$	V_{CE}=2V, I_C=5mA	25			
		$h_{FE(3)}$	V_{CE}=2V, I_C=500mA	25			
Collector-emitter saturation voltage		$V_{CE(sat)}$	I_C=500mA,I_B=50mA			0.5	V
Base-emitter voltage		V_{BE}	V_{CE}=2V, I_C=500mA			1	V

* Pulse test: pulse width ≤350μs, duty cycle≤ 2.0%.

RATINGS AND CHARACTERISTIC CURVES